Octal 3-State Noninverting Buffer/Line Driver/Line Receiver

High-Performance Silicon-Gate CMOS

The MC74HC244A is identical in pinout to the LS244. The device inputs are compatible with standard CMOS outputs; with pullup resistors, they are compatible with LSTTL outputs.

This octal noninverting buffer/line driver/line receiver is designed to be used with 3-state memory address drivers, clock drivers, and other bus-oriented systems. The device has noninverting outputs and two active-low output enables.

The HC244A is similar in function to the HC240A.

Features

- Output Drive Capability: 15 LSTTL Loads
- Outputs Directly Interface to CMOS, NMOS, and TTL
- Operating Voltage Range: 2.0 to 6.0 V
- Low Input Current: 1 μA
- High Noise Immunity Characteristic of CMOS Devices
- In Compliance with the Requirements Defined by JEDEC Standard No. 7 A
- Chip Complexity: 136 FETs or 34 Equivalent Gates
- These Devices are Pb-Free, Halogen Free and are RoHS Compliant



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MARKING DIAGRAMS

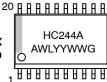


PDIP-20 N SUFFIX CASE 738

20 AAAAAAAAAAA MC74HC244AN O AWLYYWWG



SOIC-20 DW SUFFIX CASE 751D





TSSOP-20 DT SUFFIX CASE 948E





SOEIAJ-20 F SUFFIX CASE 967

A = Assembly Location

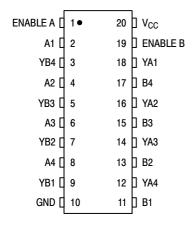
WL, L = Wafer Lot YY, Y = Year WW, W = Work Week G or ■ = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

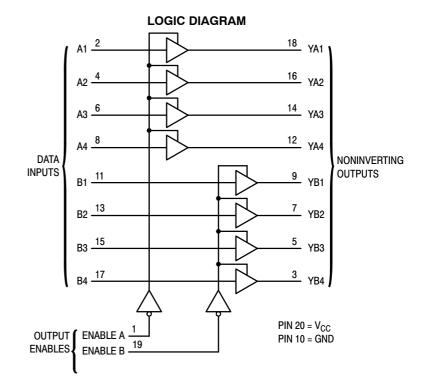
PIN ASSIGNMENT



FUNCTION TABLE

Inpu	Outputs	
Enable A, Enable B	A, B	YA, YB
L	L	L
L	Н	Н
Н	Х	Z

Z = high impedance



ORDERING INFORMATION

Device	Package	Shipping [†]
MC74HC244ANG	PDIP-20 (Pb-Free)	18 Units / Rail
MC74HC244ADWG	SOIC-20 WIDE (Pb-Free)	38 Units / Rail
MC74HC244ADWR2G	SOIC-20 WIDE (Pb-Free)	1000 Tape & Reel
MC74HC244ADTG	TSSOP-20*	75 Units / Rail
MC74HC244ADTR2G	TSSOP-20*	2500 Tape & Reel
MC74HC244AFG	SOEIAJ-20 (Pb-Free)	40 Units / Rail
MC74HC244AFELG	SOEIAJ-20 (Pb-Free)	2000 Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.
*This package is inherently Pb-Free.

MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CC}	DC Supply Voltage (Referenced to GND)	- 0.5 to + 7.0	V
V _{in}	DC Input Voltage (Referenced to GND)	-0.5 to V_{CC} + 0.5	V
V _{out}	DC Output Voltage (Referenced to GND)	-0.5 to V_{CC} + 0.5	V
I _{in}	DC Input Current, per Pin	± 20	mA
l _{out}	DC Output Current, per Pin	± 35	mA
Icc	DC Supply Current, V _{CC} and GND Pins	± 75	mA
I _{IK}	Input Clamp Current (V _I < 0 or V _I > V _{CC})	± 20	mA
lok	Output Clamp Current ($V_O < 0$ or $V_O > V_{CC}$)	± 20	mA
P _D	Power Dissipation in Still Air, Plastic DIP† SOIC Package† TSSOP Package†	750 500 450	mW
T _{stg}	Storage Temperature	- 65 to + 150	°C
TL	Lead Temperature, 1 mm from Case for 10 Seconds (Plastic DIP, SOIC, SSOP or TSSOP Package)	260	°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range GND \leq (V_{in} or V_{out}) \leq V_{CC} .

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V_{CC}). Unused outputs must be left open.

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

†Derating — Plastic DIP: – 10 mW/°C from 65° to 125°C SOIC Package: – 7 mW/°C from 65° to 125°C TSSOP Package: – 6.1 mW/°C from 65° to 125°C

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
V _{CC}	DC Supply Voltage (Referenced to GND)	2.0	6.0	V
V _{in} , V _{out}	DC Input Voltage, Output Voltage (Referenced to GND)	0	V _{CC}	V
T _A	Operating Temperature, All Package Types	- 55	+ 125	°C
t _r , t _f	Input Rise and Fall Time V_{CC} = 2.0 V (Figure 1) V_{CC} = 4.5 V V_{CC} = 6.0 V	0 0 0	1000 500 400	ns

DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

				Gu	aranteed Li	mit	
Symbol	Parameter	Test Conditions	V _{CC} V	– 55 to 25°C	≤ 85 °C	≤ 125°C	Unit
V _{IH}	Minimum High-Level Input Voltage	$\begin{aligned} V_{out} &= V_{CC} - 0.1 \text{ V} \\ I_{out} &\leq 20 \mu\text{A} \end{aligned}$	2.0 3.0 4.5 6.0	1.5 2.1 3.15 4.2	1.5 2.1 3.15 4.2	1.5 2.1 3.15 4.2	٧
V _{IL}	Maximum Low-Level Input Voltage	$\begin{aligned} V_{out} &= 0.1 \text{ V} \\ I_{out} &\leq 20 \mu\text{A} \end{aligned}$	2.0 3.0 4.5 6.0	0.5 0.9 1.35 1.8	0.5 0.9 1.35 1.8	0.5 0.9 1.35 1.8	>
V _{OH}	Minimum High-Level Output Voltage	$ \begin{aligned} &V_{in} = V_{IH} \\ & I_{out} \leq 20 \; \mu A \end{aligned} $	2.0 4.5 6.0	1.9 4.4 5.9	1.9 4.4 5.9	1.9 4.4 5.9	V
		$ \begin{aligned} V_{in} &= V_{IH} & \mid I_{out} \mid \leq 2.4 \text{ mA} \\ \mid I_{out} \mid \leq 6.0 \text{ mA} \\ \mid I_{out} \mid \leq 7.8 \text{ mA} \end{aligned} $	3.0 4.5 6.0	2.48 3.98 5.48	2.34 3.84 5.34	2.2 3.7 5.2	

DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

				Gu	aranteed Li	mit	
Symbol	Parameter	Test Conditions	V _{CC}	– 55 to 25°C	≤ 85°C	≤ 125°C	Unit
V _{OL}	Maximum Low-Level Output Voltage	$V_{in} = V_{IL}$ $ I_{out} \le 20 \ \mu A$	2.0 4.5 6.0	0.1 0.1 0.1	0.1 0.1 0.1	0.1 0.1 0.1	V
		$ \begin{array}{c c} V_{in} = V_{IL} & I_{out} \leq 2.4 \text{ mA} \\ & I_{out} \leq 6.0 \text{ mA} \\ & I_{out} \leq 7.8 \text{ mA} \end{array} $	3.0 4.5 6.0	0.26 0.26 0.26	0.33 0.33 0.33	0.4 0.4 0.4	
I _{in}	Maximum Input Leakage Current	V _{in} = V _{CC} or GND	6.0	± 0.1	± 1.0	± 1.0	μΑ
l _{OZ}	Maximum Three-State Leakage Current	Output in High-Impedance State $V_{in} = V_{IL}$ or V_{IH} $V_{out} = V_{CC}$ or GND	6.0	± 0.5	± 5.0	± 10	μΑ
I _{CC}	Maximum Quiescent Supply Current (per Package)	$V_{in} = V_{CC}$ or GND $I_{out} = 0 \mu A$	6.0	4.0	40	160	μΑ

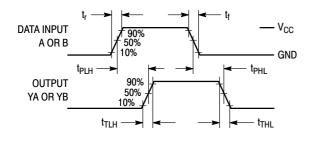
AC ELECTRICAL CHARACTERISTICS (C_L = 50 pF, Input t_r = t_f = 6 ns)

			Gu	aranteed Li	mit	
Symbol	Parameter	V _{CC}	– 55 to 25°C	≤ 85 °C	≤125°C	Unit
t _{PLH} , t _{PHL}	Maximum Propagation Delay, A to YA or B to YB (Figures 1 and 3)	2.0 3.0 4.5 6.0	96 50 18 15	115 60 23 20	135 70 27 23	ns
t _{PLZ} , t _{PHZ}	Maximum Propagation Delay, Output Enable to YA or YB (Figures 2 and 4)	2.0 3.0 4.5 6.0	110 60 22 19	140 70 28 24	165 80 33 28	ns
t _{PZL} , t _{PZH}	Maximum Propagation Delay, Output Enable to YA or YB (Figures 2 and 4)	2.0 3.0 4.5 6.0	110 60 22 19	140 70 28 24	165 80 33 28	ns
t _{TLH} , t _{THL}	Maximum Output Transition Time, Any Output (Figures 1 and 3)	2.0 3.0 4.5 6.0	60 23 12 10	75 27 15 13	90 32 18 15	ns
C _{in}	Maximum Input Capacitance	-	10	10	10	pF
C _{out}	Maximum Three-State Output Capacitance (Output in High-Impedance State)	-	15	15	15	pF

		Typical @ 25°C, V _{CC} = 5.0 V	
C_{PD}	Power Dissipation Capacitance (Per Buffer)*	34	pF

^{*}Used to determine the no–load dynamic power consumption: $P_D = C_{PD} V_{CC}^2 f + I_{CC} V_{CC}$.

SWITCHING WAVEFORMS

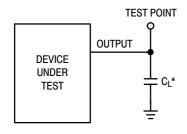


 V_{CC} **ENABLE** A OR B **GND** -t_{PZL} t_{PLZ} HIGH **IMPEDANCE** 50% **OUTPUT Y** 10% V_{OL} t_{PZH} t_{PHZ} 90% V_{OH} **OUTPUT Y** 50% HIGH **IMPEDANCE**

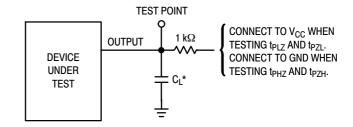
Figure 1.

Figure 2.

TEST CIRCUITS



*Includes all probe and jig capacitance



*Includes all probe and jig capacitance

Figure 3. Test Circuit

Figure 4. Test Circuit

PIN DESCRIPTIONS

INPUTS

A1, A2, A3, A4, B1, B2, B3, B4 (Pins 2, 4, 6, 8, 11, 13, 15, 17)

Data input pins. Data on these pins appear in noninverted form on the corresponding Y outputs, when the outputs are enabled.

CONTROLS

Enable A, Enable B (Pins 1, 19)

Output enables (active-low). When a low level is applied to these pins, the outputs are enabled and the devices

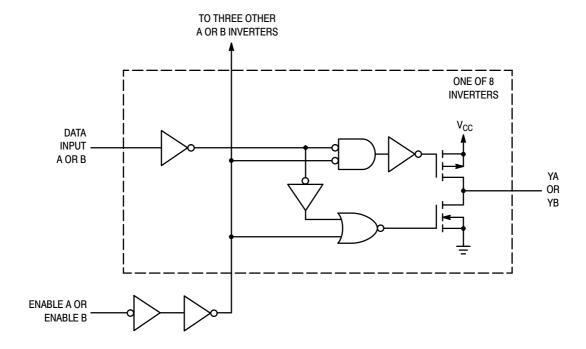
function as noninverting buffers. When a high level is applied, the outputs assume the high impedance state.

OUTPUTS

YA1, YA2, YA3, YA4, YB1, YB2, YB3, YB4 (Pins 18, 16, 14, 12, 9, 7, 5, 3)

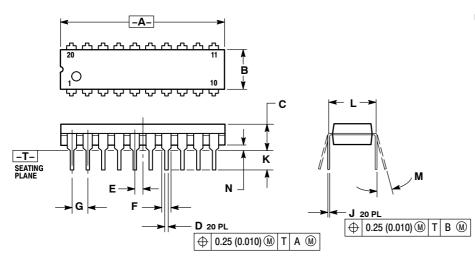
Device outputs. Depending upon the state of the output-enable pins, these outputs are either noninverting outputs or high-impedance outputs.

LOGIC DETAIL



PACKAGE DIMENSIONS

PDIP-20 **N SUFFIX** PLASTIC DIP PACKAGE CASE 738-03 ISSUE E



NOTES:

- IOTES:

 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

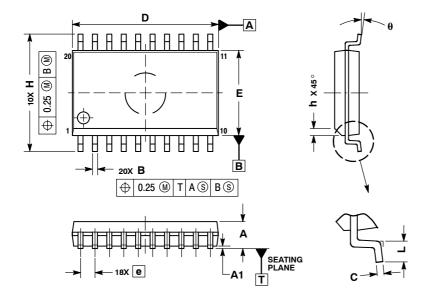
 2. CONTROLLING DIMENSION: INCH.

 3. DIMENSION L TO CENTER OF LEAD WHEN FORMED PARALLEL.

 4. DIMENSION B DOES NOT INCLUDE MOLD FLASH.

	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	1.010	1.070	25.66	27.17
В	0.240	0.260	6.10	6.60
С	0.150	0.180	3.81	4.57
D	0.015	0.022	0.39	0.55
E	0.050	BSC	1.27 BSC	
F	0.050	0.070	1.27	1.77
G	0.100	0.100 BSC		BSC
J	0.008	0.015	0.21	0.38
K	0.110	0.140	2.80	3.55
L	0.300 BSC		7.62	BSC
М	0°	15°	0°	15°
N	0.020	0.040	0.51	1.01

SOIC-20 **DW SUFFIX** CASE 751D-05 **ISSUE G**



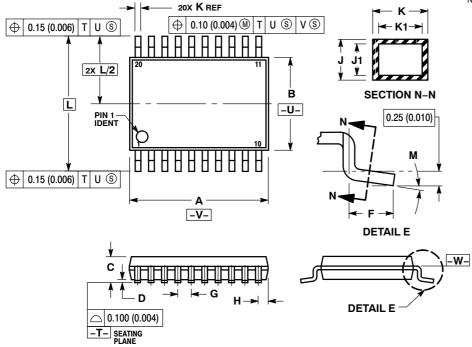
NOTES:

- DTES:
 DIMENSIONS ARE IN MILLIMETERS.
 INTERPRET DIMENSIONS AND TOLERANCES
 PER ASME Y14.5M, 1994.
 DIMENSIONS D AND E DO NOT INCLUDE MOLD
 PROTRUSION.
 MAXIMUM MOLD PROTRUSION 0.15 PER SIDE.
 DIMENSION B DOES NOT INCLUDE DAMBAR
 PROTRUSION. ALLOWABLE PROTRUSION
 SHALL BE 0.13 TOTAL IN EXCESS OF B
 DIMENSION AT MAXIMUM MATERIAL
 CONDITION.

	MILLIMETERS			
DIM	MIN	MAX		
Α	2.35	2.65		
A1	0.10	0.25		
В	0.35	0.49		
C	0.23	0.32		
D	12.65	12.95		
E	7.40	7.60		
е	1.27	BSC		
Н	10.05	10.55		
h	0.25	0.75		
L	0.50	0.90		
θ	0 °	7 °		

PACKAGE DIMENSIONS

TSSOP-20 **DT SUFFIX** CASE 948E-02 ISSUE C

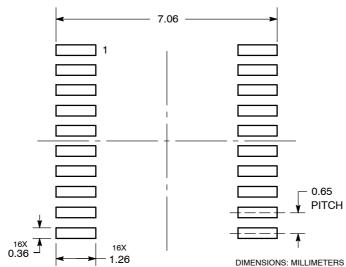


- NOTES:

 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION:
 MILLIMETER.
 3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS. SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
 4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION. SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
 5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
 6. TERMINAL NUMBERS ARE SHOWN FOR
 - 6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY. 7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE –W–.

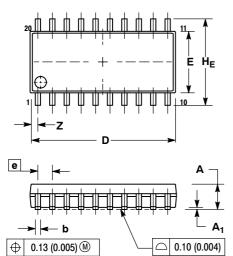
	MILLIN	IETERS	INC	HES	
DIM	MIN	MAX	MIN	MAX	
Α	6.40	6.60	0.252	0.260	
В	4.30	4.50	0.169	0.177	
С		1.20		0.047	
D	0.05	0.15	0.002	0.006	
F	0.50	0.75	0.020	0.030	
G	0.65 BSC		0.026	BSC	
Н	0.27	0.37	0.011	0.015	
J	0.09	0.20	0.004	0.008	
J1	0.09	0.16	0.004	0.006	
K	0.19	0.30	0.007	0.012	
K1	0.19	0.25	0.007	0.010	
L	6.40	BSC	0.252 BSC		
M	0°	8°	0°	8°	

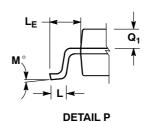
SOLDERING FOOTPRINT

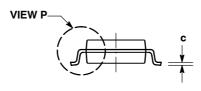


PACKAGE DIMENSIONS

SOEIAJ-20 **F SUFFIX** CASE 967-01 **ISSUE A**







NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI
- DIMENSIONING AUTO . .
 Y14.5M, 1982.
 CONTROLLING DIMENSION: MILLIMETER.
 DIMENSIONS D AND E DO NOT INCLUDE
 MENSIONS D AND E DO NOT INCLUDE
 AND ARE
- MOLD FLASH OR PROTRUSIONS AND ARE MEASURED AT THE PARTING LINE, MOLD FLASH OR PROTRUSIONS SHALL NOT EXCEED 0.15 (0.006) PER SIDE. 4. TERMINAL NUMBERS ARE SHOWN FOR
- REFERENCE ONLY. 5. THE LEAD WIDTH DIMENSION (b) DOES NOT
- INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE LEAD WIDTH
 DIMENSION AT MAXIMUM MATERIAL CONDITION. DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OR THE FOOT MINIMUM SPACE BETWEEN PROTRUSIONS AND ADJACENT LEAD TO BE 0.46 (0.018).

		-,		
	MILLIN	IETERS	INC	HES
DIM	MIN	MAX	MIN	MAX
Α		2.05		0.081
A ₁	0.05	0.20	0.002	0.008
b	0.35	0.50	0.014	0.020
С	0.15	0.25	0.006	0.010
D	12.35	12.80	0.486	0.504
Е	5.10	5.45	0.201	0.215
е	1.27	BSC	0.050	BSC
HE	7.40	8.20	0.291	0.323
L	0.50	0.85	0.020	0.033
LΕ	1.10	1.50	0.043	0.059
M	0 °	10 °	0 °	10°
Q_1	0.70	0.90	0.028	0.035
Z		0.81		0.032

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